

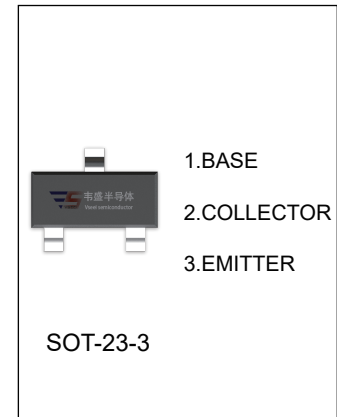
2SD1781 TRANSISTOR (NPN)

FEATURES

- Very low $V_{CE(sat)}$. $V_{CE(sat)} < 0.4$ V (Typ.) ($I_C / I_B = 500\text{mA} / 50\text{mA}$)
- Complements to 2SB1197.

MAXIMUM RATINGS ($T_a=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	40	V
V_{CEO}	Collector-Emitter Voltage	32	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current	800	mA
P_C	Collector Power Dissipation	200	mW
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	625	$^\circ\text{C}/\text{W}$
T_J, T_{stg}	Operation Junction and Storage Temperature Range	-55~+150	$^\circ\text{C}$



ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=50\mu\text{A}, I_E=0$	40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1\text{mA}, I_B=0$	32			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=50\mu\text{A}, I_C=0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB}=20\text{V}, I_E=0$			0.5	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=4\text{V}, I_C=0$			0.5	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=3\text{V}, I_C=100\text{mA}$	120		390	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=500\text{mA}, I_B=50\text{mA}$			0.4	V
Transition frequency	f_T	$V_{CE}=5\text{V}, I_C=50\text{mA}, f=100\text{MHz}$		150		MHz
Collector output capacitance	C_{ob}	$V_{CB}=10\text{V}, I_E=0, f=1\text{MHz}$		10		pF

CLASSIFICATION OF $h_{FE(1)}$

Rank	Q	R
Range	120-270	180-390
Marking	AFQ	AFR

Static Characteristic
